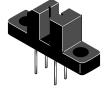


PACKAGE DIMENSIONS 0.972 (24.7) 0.957 (24.3) 0.472 (12.0) 0.457 (11.6) 0.249 (6.35) 0.243 (6.15) 0.755 (19.2) 0.745 (18.9) 0.129 (3.3) 0.119 (3.0) 0.315 (8.0) 0.100 (0.51) (SQ) PIN 1 ANODE PIN 2 CATHODE PIN 3 COLLECTOR PIN 4 EMITTER NOTES:

- Dimensions for all drawings are in inches (mm).
- 2. Tolerance of ± .010 (.25) on all non-nominal dimensions unless otherwise specified.

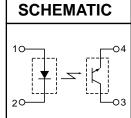
DESCRIPTION

The H21A1, H21A2 and H21A3 consist of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor in a plastic housing. The packaging system is designed to optimize the mechanical resolution, coupling efficiency, ambient light rejection, cost and reliability. The gap in the housing provides a means of interrupting the signal with an opaque material, switching the output from an "ON" to an "OFF" state.



FEATURES

- Opaque housing
- Low cost
- .035" apertures
- High I_{C(ON)}



- 1. Derate power dissipation linearly 1.33 mW/°C above 25°C.
- 2. RMA flux is recommended.
- Methanol or isopropyl alcohols are recommended as cleaning agents.
- 4. Soldering iron tip 1/16" (1.6mm) minimum from housing.

Parameter	Symbol	Rating	Unit	
Operating Temperature	T _{OPR}	-55 to +100	°C	
Storage Temperature	T _{STG}	-55 to +100	°C	
Soldering Temperature (Iron)(2,3 and 4)	T _{SOL-I}	240 for 5 sec	°C	
Soldering Temperature (Flow) ^(2 and 3)	T _{SOL-F}	260 for 10 sec	°C	
INPUT (EMITTER)	l-	50	^	
Continuous Forward Current	lF	50	mA	
Reverse Voltage	V _R	6	V	
Power Dissipation (1)	P _D	100	mW	
OUTPUT (SENSOR)	.,,	00	V	
Collector to Emitter Voltage	V _{CEO}	30	V	
Emitter to Collector Voltage	V _{ECO}	4.5	V	
Collector Current	I _C	20	mA	
Power Dissipation (T _C = 25°C) ⁽¹⁾	P _D	150	mW	



ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C)(All measurements made under pulse condition)										
PARAMETER	TEST CONDITIONS	SYMBOL	DEVICES	MIN	TYP	MAX	UNITS			
INPUT (EMITTER) Forward Voltage	I _F = 60 mA	VF	All	_	_	1.7	V			
Reverse Breakdown Voltage	I _R = 10 μA	V_R	All	6.0	_	_	V			
Reverse Leakage Current	V _R = 3 V	I _R	All	_	_	1.0	μA			
OUTPUT (SENSOR) Emitter to Collector Breakdown	$I_F = 100 \mu A, Ee = 0$	BV _{ECO}	All	6.0		_	V			
Collector to Emitter Breakdown	$I_{\rm C} = 1 \text{ mA, Ee} = 0$	BV _{CEO}	All	30	_	_	V			
Collector to Emitter Leakage	V _{CE} = 25 V, Ee = 0	I _{CEO}	All	_	_	100	nA			
COUPLED	I _F = 5 mA, V _{CE} = 5 V	I _{C(ON)}	H21A1	0.15	_	_	mA			
On-State Collector Current			H21A2	0.30	_	_				
			H21A3	0.60	_	_				
	$I_F = 20 \text{ mA}, V_{CE} = 5 \text{ V}$		H21A1	1.0	_	_				
			H21A2	2.0	_	_				
			H21A3	4.0						
			H21A1	1.9	_	_				
	$I_F = 30 \text{ mA}, V_{CE} = 5 \text{ V}$		H21A2	3.0	_	_				
			H21A3	5.5	_	_				
Saturation Voltage	$I_F = 20 \text{ mA}, I_C = 1.8 \text{ mA}$	VCE(SAT)	H21A2/3	_	_	0.40	V			
	$I_F = 30 \text{ mA}, I_C = 1.8 \text{ mA}$		H21A1		_	0.40	V			
Turn-On Time	$I_F = 30$ mA, $V_{CC} = 5$ V, $R_L = 2.5$ K Ω	t _{on}	All		8		μs			
Turn-Off Time	$I_F = 30$ mA, $V_{CC} = 5$ V, $R_L = 2.5$ K Ω	t _{off}	All		50	_	μs			



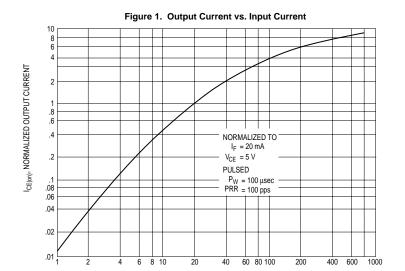
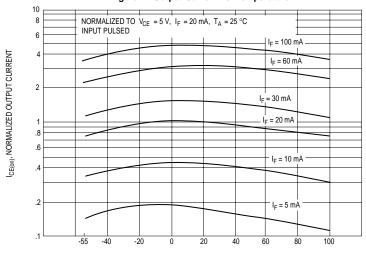


Figure 2. Output Current vs. Temperature

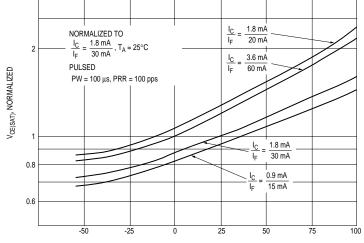
IF, INPUT CURRENT (mA)



T_A, AMBIENT TEMPERATURE (°C)

Figure 3. V_{CE(SAT)} vs. Temperature

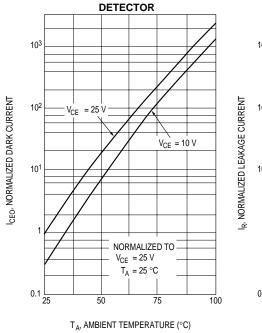


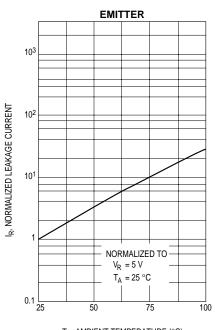


TA, AMBIENT TEMPERATURE (°C)



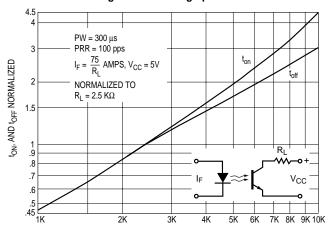
Figure 4. Leakage Current vs. Temperature



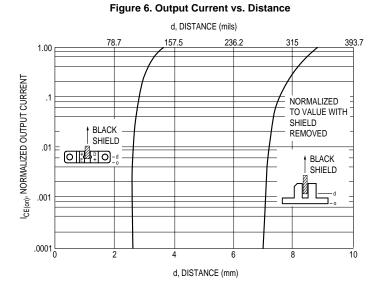


T_A, AMBIENT TEMPERATURE (°C)

Figure 5. Switching Speed vs. RL



 R_L , LOAD RESISTANCE (Ω)



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